



DMG6968U

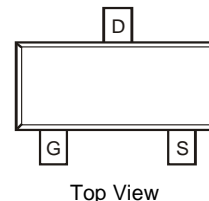
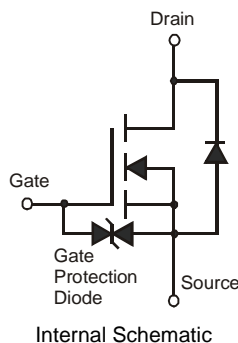
N-CHANNEL ENHANCEMENT MODE MOSFET

Features

- Low On-Resistance
 - 25mΩ @ $V_{GS} = 4.5V$
 - 29mΩ @ $V_{GS} = 2.5V$
 - 36mΩ @ $V_{GS} = 1.8V$
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- **ESD Protected Up To 2kV**
- **Lead Free By Design/RoHS Compliant (Note 1)**
- **"Green" Device (Note 2)**
- **Qualified to AEC-Q101 Standards for High Reliability**

Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Terminals Connections: See Diagram Below
- Weight: 0.008 grams (approximate)

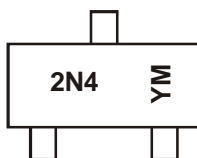


Ordering Information (Note 3)

Part Number	Qualification	Case	Packaging
DMG6968U-7	Commercial	SOT23	3000/Tape & Reel
DMG6968UQ-7	Automotive	SOT23	3000/Tape & Reel

Notes: 1. No purposefully added lead.

Marking Information



2N4 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: W = 2009)
 M = Month (ex: 9 = September)

Date Code Key

Year	2009	2010	2011	2012	2013	2014	2015
Code	W	X	Y	Z	A	B	C

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D



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Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	20	V
Gate-Source Voltage			V _{GSS}	±12	V
Continuous Drain Current (Note 4)	Steady State	T _A = 25°C	I _D	6.5	A
		T _A = 70°C		5.2	
Pulsed Drain Current			I _{DM}	30	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 4)	P _D	1.3	W
Thermal Resistance, Junction to Ambient @T _A = 25°C	R _{θJA}	157	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 5)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	—	—	V	V _{GS} = 0V, I _D = 250μA
Zero Gate Voltage Drain Current	I _{DSS}	—	—	1.0	μA	V _{DS} = 20V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	±10	μA	V _{GS} = ±10V, V _{DS} = 0V
Gate-Source Breakdown Voltage	BV _{S_{GS}}	±12	-	-	V	V _{DS} = 0V, I _G = ±250μA
ON CHARACTERISTICS (Note 5)						
Gate Threshold Voltage	V _{GS(th)}	0.5	—	0.9	V	V _{DS} = V _{GS} , I _D = 250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	21	25	mΩ	V _{GS} = 4.5V, I _D = 6.5A
			23	29		V _{GS} = 2.5V, I _D = 5.5A
			28	36		V _{GS} = 1.8V, I _D = 3.5A
Forward Transfer Admittance	Y _{fs}	—	8	—	S	V _{DS} = 10V, I _D = 5A
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iSS}	—	151	—	pF	V _{DS} = 10V, V _{GS} = 0V f = 1.0MHz
Output Capacitance	C _{oss}	—	91	—	pF	
Reverse Transfer Capacitance	C _{rSS}	—	32	—	pF	
Total Gate Charge	Q _g	—	8.5	—	nC	V _{GS} = 4.5V, V _{DS} = 10V, I _D = 6.5A
Gate-Source Charge	Q _{gs}	—	1.6	—	nC	
Gate-Drain Charge	Q _{gd}	—	2.8	—	nC	
Turn-On Delay Time	t _{D(on)}	—	54	—	ns	V _{DD} = 10V, V _{GS} = 4.5V, R _L = 10Ω, R _G = 6Ω, I _D = 1A
Turn-On Rise Time	t _r	—	66	—	ns	
Turn-Off Delay Time	t _{D(off)}	—	613	—	ns	
Turn-Off Fall Time	t _f	—	205	—	ns	

Notes: 2. Device mounted on FR-4 substrate PC board, 2oz. copper, with thermal vias to bottom layer 1 inch square copper plate.
3. Short duration pulse test used to minimize self-heating effect.